Unit: mm

4.0±0.2

0.45+0.1

1: Emitter 2: Collector 3: Base EIAJ: SC-43A TO-92-B1 Package

5.0±0.2

# 2SC2631

## Silicon NPN epitaxial planar type

For low-frequency high breakdown voltage amplification Complementary to 2SA1123

#### Features

- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- High collector-emitter voltage (Base open) V<sub>CEO</sub>
- Small collector output capacitance (Common base, input open cir cuited) Cob

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

	- a			
Parameter	Symbol	Rating	Unit	$0.45^{+0.15}_{-0.1}$
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	150	V	<u>2.5_0.2</u> 2.5_0.2
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	150	v	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V	5340
Collector current	Ι <sub>C</sub>	50	mA	
Peak collector current	I <sub>CP</sub>	100	mA	<u>2012</u>
Collector power dissipation	P <sub>C</sub>	750	mW	NILLER
Junction temperature	Tj	150	ୁ ଦ୍	
Storage temperature	T <sub>stg</sub>	-55 to +150	<u>6</u>	a dr. dr

I <sub>CP</sub>		- AV
P <sub>C</sub>	750 mW	nº.
Tj		
T <sub>stg</sub> -	-55 to +150 500 x x x x x	
,= 25°C	±320 mainten cented ve latester	
Symbol	Conditions Min Typ Max	Unit
VEO	$I_{c} = 100 \ \mu A_{c} I_{B} = 0$ 150	V
W <sub>EBO</sub>	$I_{\rm E} = 10 \mu{\rm A}, I_{\rm C} \ge 0$	V
I <sub>CBO</sub>	$V_{CB} = 100 V_{cB} = 0$ 1	μΑ
h <sub>FE</sub>	$V_{CE} = 50, I_C = 10 \text{ mA}$ 130 330	_
V <sub>CE(sat)</sub>	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 3 \text{ mA}$ 1	V
f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$ 160	MHz
C <sub>ob</sub>	$V_{CB} = 10 V_{v} I_{E} = 0, f = 1 MHz$ 3	pF
	ight Mt	
NV	$V_{CE} = 40 \text{ V}, I_C = 1 \text{ mA}, G_V = 80 \text{ dB}$ 150 300	mV
	$R_g \simeq 100 \text{ k}\Omega$ , Function = FLAT	
	$\begin{array}{c} P_{C} \\ T_{J} \\ T_{stg} \\ \end{array}$	C 750 mW   Tj 150 °C   T_{stg} -55 to +150 °C   Symbol Conditions Min Typ Max   Vebo Ic=100 $\mu$ A, Ic=0 55 150 150 160   Vebo Ic=10 $\mu$ A, Ic=0 55 110 100 110   Vebo Ic=10 $\mu$ A, Ic=0 55 110 110 110   Vebo Ic=30 $\mu$ A, Ic=10 $\mu$ A, Ic=0 110 110 330 110   Vccso Ic=30 $\mu$ A, Is=3 $\mu$ A 110 330 330 110   Vcte(sat) Ic=30 $\mu$ A, Is=0, f=10 $\mu$ A, f=200 $\mu$ A and the state of the

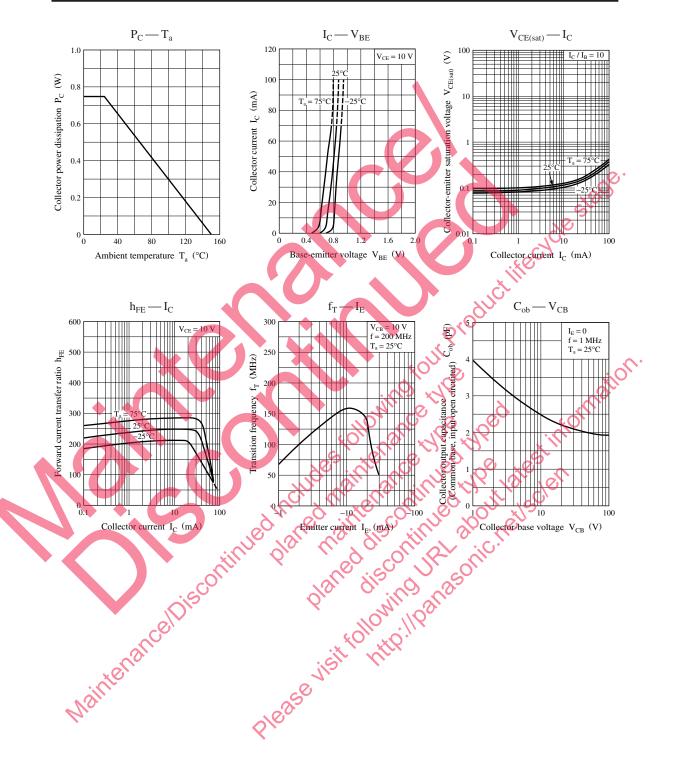
Note Measuring methods are based on JAPANESEINDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	R	S
h <sub>FE</sub>	130 to 220	185 to 330

### 2SC2631





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